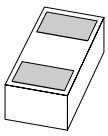


BAP55LX

Silicon PIN diode

Rev. 01 — 30 July 2007 **Product data sheet**

1. Product profile

1.1 General description

Planar PIN diode in a SOD882T leadless ultra small plastic SMD package.

1.2 Features

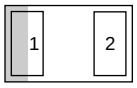
- High speed switching for RF signals
- Low diode capacitance
- Low forward resistance
- Very low series inductance
- For applications up to 3 GHz

1.3 Applications

- RF attenuators and switches

2. Pinning information

Table 1. Discrete pinning

Pin	Description	Simplified outline	Symbol
1	cathode [1]	 Transparent top view	 sym006
2	anode		

[1] The marking bar indicates the cathode.

3. Ordering information

Table 2. Ordering information

Type number	Package		
	Name	Description	Version
BAP55LX	-	leadless ultra small plastic package; 2 terminals; body 1 × 0.6 × 0.4 mm	SOD882T

4. Marking

Table 3. Marking

Type number	Marking code
BAP55LX	LC

5. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_R	reverse voltage		-	50	V
I_F	forward current		-	100	mA
P_{tot}	total power dissipation	T_{sp} = 90 °C	-	135	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–65	+150	°C

6. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Typ	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point		78	K/W

7. Characteristics

Table 6. Characteristics

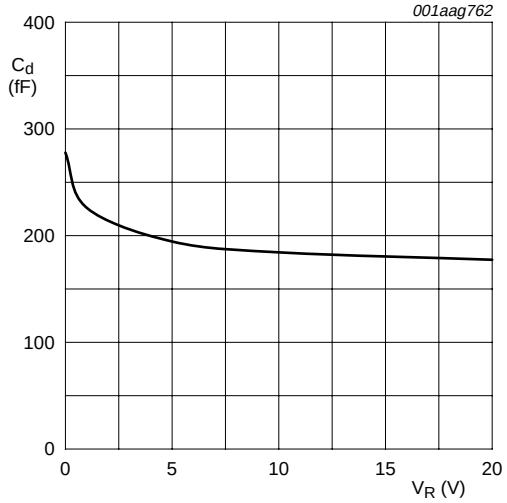
T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_F	forward voltage	I_F = 50 mA	-	0.95	1.1	V
I_R	reverse current	V_R = 20 V	-	-	10	nA
		V_R = 50 V	-	-	100	nA
C_d	diode capacitance	see Figure 1; f = 1 MHz;				
		V_R = 0 V	-	0.28	-	pF
		V_R = 1 V	-	0.23	-	pF
		V_R = 20 V	-	0.18	0.28	pF
r_D	diode forward resistance	see Figure 2; f = 100 MHz;				
		I_F = 0.5 mA	-	3.3	4.5	Ω
		I_F = 1 mA	-	2.2	3.3	Ω
		I_F = 10 mA	-	0.8	1.2	Ω
		I_F = 100 mA	-	0.5	0.8	Ω

Table 6. Characteristics *...continued*

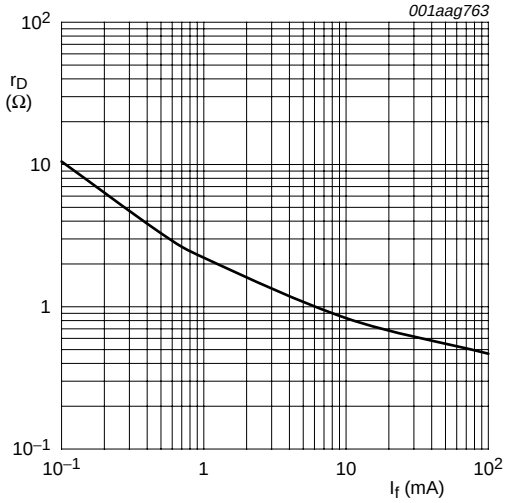
T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
ISL	isolation	see Figure 3; V_R = 0 V;				
		f = 900 MHz	-	19	-	dB
		f = 1800 MHz	-	14	-	dB
		f = 2450 MHz	-	12	-	dB
L_{ins}	insertion loss	see Figure 4; I_F = 0.5 mA;				
		f = 900 MHz	-	0.24	-	dB
		f = 1800 MHz	-	0.25	-	dB
		f = 2450 MHz	-	0.26	-	dB
L_{ins}	insertion loss	see Figure 4; I_F = 1 mA;				
		f = 900 MHz	-	0.17	-	dB
		f = 1800 MHz	-	0.18	-	dB
		f = 2450 MHz	-	0.19	-	dB
L_{ins}	insertion loss	see Figure 4; I_F = 10 mA;				
		f = 900 MHz	-	0.08	-	dB
		f = 1800 MHz	-	0.09	-	dB
		f = 2450 MHz	-	0.10	-	dB
L_{ins}	insertion loss	see Figure 4; I_F = 100 mA;				
		f = 900 MHz	-	0.05	-	dB
		f = 1800 MHz	-	0.07	-	dB
		f = 2450 MHz	-	0.08	-	dB
τ_L	charge carrier life time	when switched from I_F = 10 mA to I_R = 6 mA; R_L = 100 Ω; measured at I_R = 3 mA	-	0.27	-	µs
L_S	series inductance	I_F = 100 mA; f = 100 MHz	-	0.4	-	nH



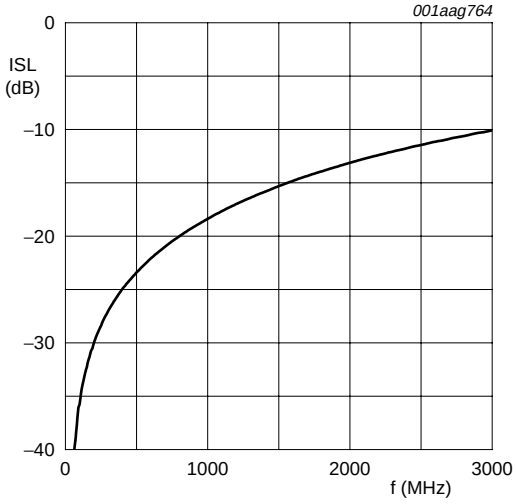
f = 1 MHz; T_j = 25 °C.

Fig 1. Diode capacitance as a function of reverse voltage; typical values



f = 100 MHz; T_j = 25 °C.

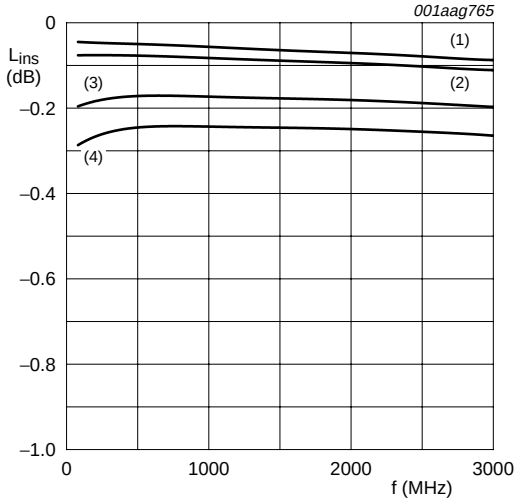
Fig 2. Forward resistance as a function of forward current; typical values



T_{amb} = 25 °C

Diode zero biased and inserted in series with a 50 Ω stripline circuit

Fig 3. Isolation of the diode as a function of frequency; typical values



T_{amb} = 25 °C

(1) I_F = 100 mA

(2) I_F = 10 mA

(3) I_F = 1 mA

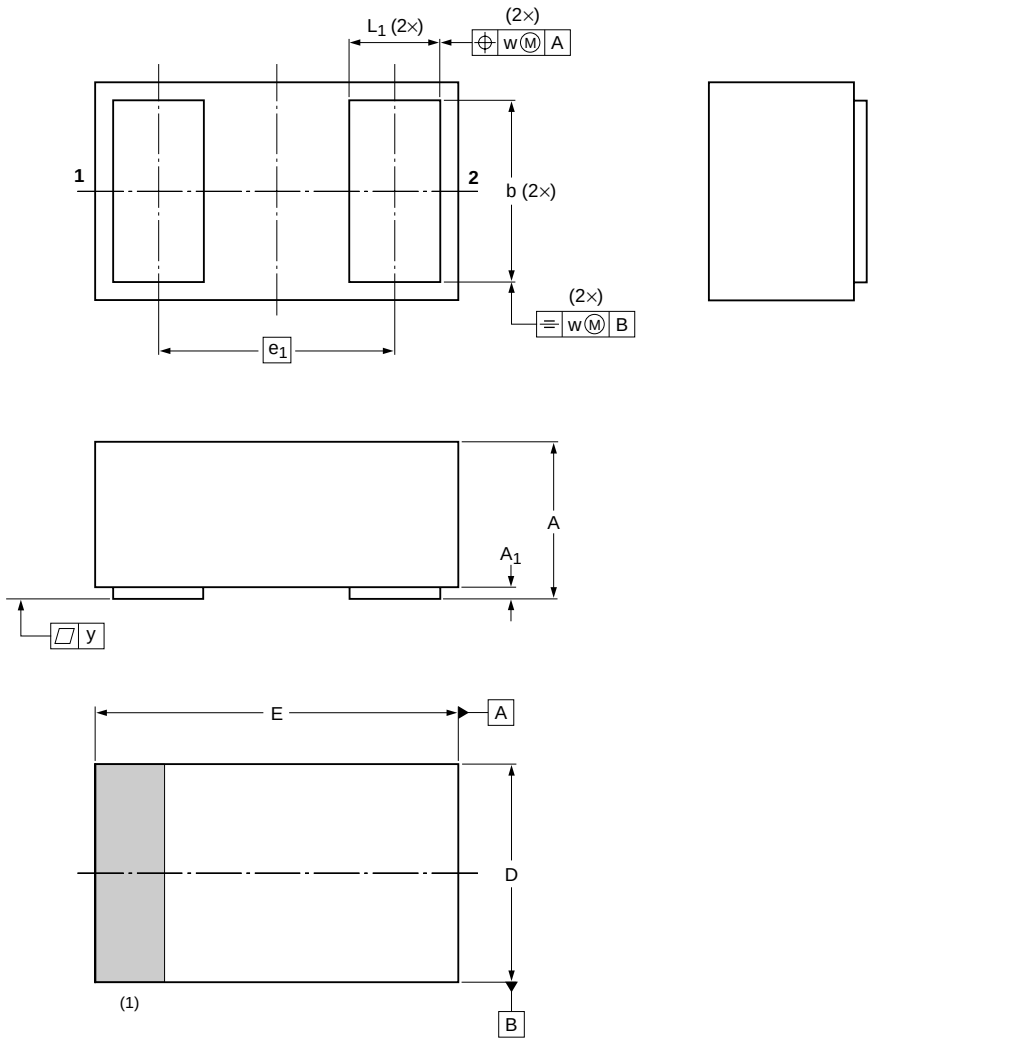
(4) I_F = 0.5 mA

Diode inserted in series with a 50 Ω stripline circuit and biased via the analyzer Tee network

Fig 4. Insertion loss of the diode as a function of frequency; typical values

8. Package outline

Leadless ultra small plastic package; 2 terminals; body 1 x 0.6 x 0.4 mm **SOD882T**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max	b	D	E	e_1	L_1	w	y
mm	0.40 0.36	0.04	0.55 0.45	0.65 0.55	1.05 0.95	0.65	0.30 0.22	0.1	0.03

Note

1. The marking bar indicates the cathode

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOD882T						~~04-12-14~~ 06-04-12

Fig 5. Package outline SOD882T

9. Abbreviations

Table 7. Abbreviations

Acronym	Description
PIN	P-type, Intrinsic, N-type
SMD	Surface Mounted Device
RF	Radio Frequency

10. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BAP55LX_1	20070730	Product data sheet	-	-

11. Legal information

11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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